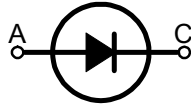
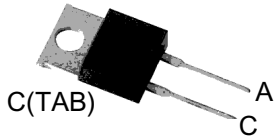


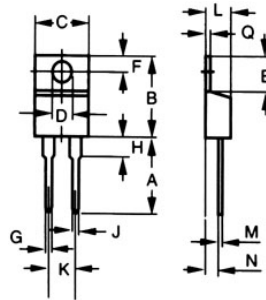
SUR20100 thru SUR20120

Ultra Fast Recovery Epitaxial Diodes



A=Anode, C=Cathode, TAB=Cathode

Dimensions TO-220AC



Dim.	Inches		Milimeter	
	Min.	Max.	Min.	Max.
A	0.500	0.580	12.70	14.73
B	0.560	0.650	14.23	16.51
C	0.380	0.420	9.66	10.66
D	0.139	0.161	3.54	4.08
E	2.300	0.420	5.85	6.85
F	0.100	0.135	2.54	3.42
G	0.045	0.070	1.15	1.77
H	-	0.250	-	6.35
J	0.025	0.035	0.64	0.89
K	0.190	0.210	4.83	5.33
L	0.140	0.190	3.56	4.82
M	0.015	0.022	0.38	0.56
N	0.080	0.115	2.04	2.49
Q	0.025	0.055	0.64	1.39

	V_{RSM}	V_{RRM}
	V	V
SUR20100	1000	1000
SUR20120	1200	1200

Symbol	Test Conditions	Maximum Ratings	Unit
I_{FRMS}	$T_{VJ}=T_{VJM}$	70	A
I_{FAVM}	$T_C=85^\circ\text{C}$; rectangular, $d=0.5$	17	
I_{FRM}	$t_p < 10\mu\text{s}$; rep. rating, pulse width limited by T_{VJM}	220	
I_{FSM}	$T_{VJ}=45^\circ\text{C}$	$t=10\text{ms}$ (50Hz), sine $t=8.3\text{ms}$ (60Hz), sine	A
	$T_{VJ}=150^\circ\text{C}$	$t=10\text{ms}$ (50Hz), sine $t=8.3\text{ms}$ (60Hz), sine	
I^2t	$T_{VJ}=45^\circ\text{C}$	$t=10\text{ms}$ (50Hz), sine $t=8.3\text{ms}$ (60Hz), sine	A^2s
	$T_{VJ}=150^\circ\text{C}$	$t=10\text{ms}$ (50Hz), sine $t=8.3\text{ms}$ (60Hz), sine	
T_{VJ} T_{VJM} T_{stg}		-40...+150 150 -40...+150	$^\circ\text{C}$
P_{tot}	$T_C=25^\circ\text{C}$	78	W
M_d	Mounting torque	0.4...0.6	Nm
Weight		2	g

SUR20100 thru SUR20120

Ultra Fast Recovery Epitaxial Diodes

Symbol	Test Conditions	Characteristic Values		Unit
		typ.	max.	
I_R	$T_{VJ}=25^{\circ}\text{C}; V_R=V_{RRM}$		750	uA
	$T_{VJ}=25^{\circ}\text{C}; V_R=0.8 \cdot V_{RRM}$		250	uA
	$T_{VJ}=125^{\circ}\text{C}; V_R=0.8 \cdot V_{RRM}$		7	mA
V_F	$I_F=12\text{A}; T_{VJ}=150^{\circ}\text{C}$		1.87	V
	$T_{VJ}=25^{\circ}\text{C}$		2.15	
V_{TO}	For power-loss calculations only		1.65	V
r_T	$T_{VJ}=T_{VJM}$		18.2	m Ω
R_{thJC} R_{thJA}			1.6	K/W
			60	
t_{rr}	$I_F=1\text{A}; -di/dt=100\text{A/us}; V_R=30\text{V}; T_{VJ}=25^{\circ}\text{C}$	40	60	ns
I_{RM}	$V_R=540\text{V}; I_F=20\text{A}; -di_F/dt=100\text{A/us}; L \leq 0.05\mu\text{H}; T_{VJ}=100^{\circ}\text{C}$	7		A

FEATURES

- * International standard package
- * Glass passivated chips
- * Very short recovery time
- * Extremely low losses at high switching frequencies
- * Low I_{RM}-values
- * Soft recovery behaviour

APPLICATIONS

- * Antiparallel diode for high frequency switching devices
- * Anti saturation diode
- * Snubber diode
- * Free wheeling diode in converters and motor control circuits
- * Rectifiers in switch mode power supplies (SMPS)
- * Inductive heating and melting
- * Uninterruptible power supplies (UPS)
- * Ultrasonic cleaners and welders

ADVANTAGES

- * High reliability circuit operation
- * Low voltage peaks for reduced protection circuits
- * Low noise switching
- * Low losses
- * Operating at lower temperature or space saving by reduced cooling

SUR20100 thru SUR20120

Ultra Fast Recovery Epitaxial Diodes

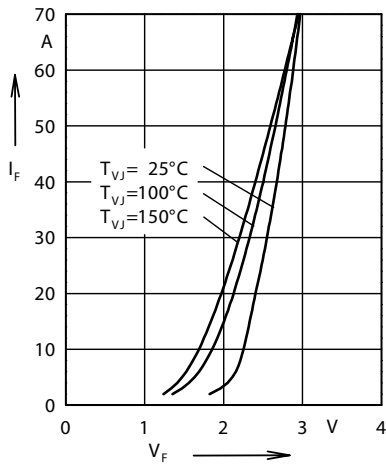


Fig. 1 Forward current versus voltage drop.

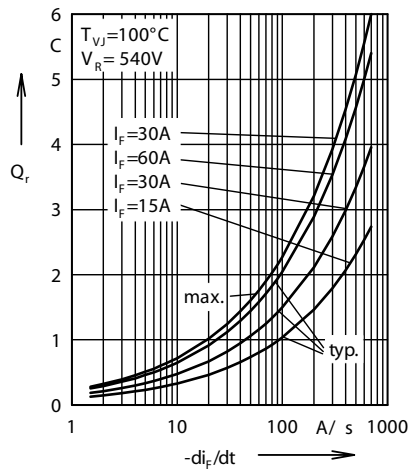


Fig. 2 Recovery charge versus $-di_F/dt$.

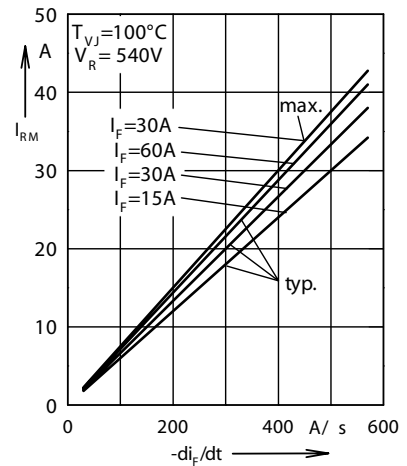


Fig. 3 Peak reverse current versus $-di_F/dt$.

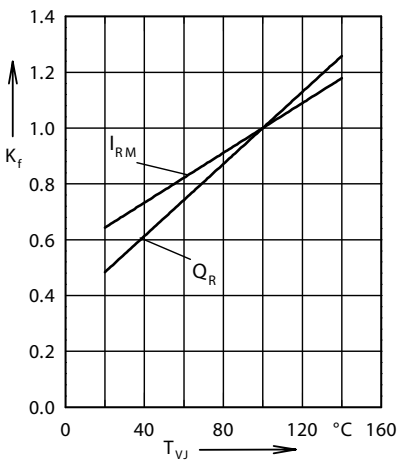


Fig. 4 Dynamic parameters versus junction temperature.

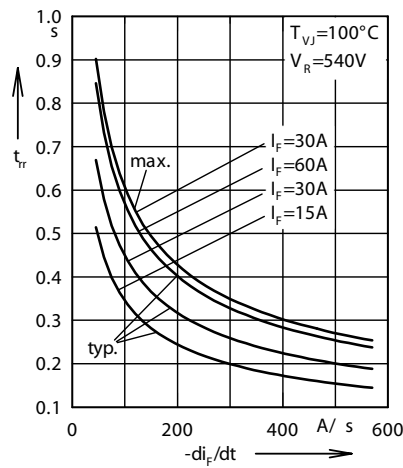


Fig. 5 Recovery time versus $-di_F/dt$.

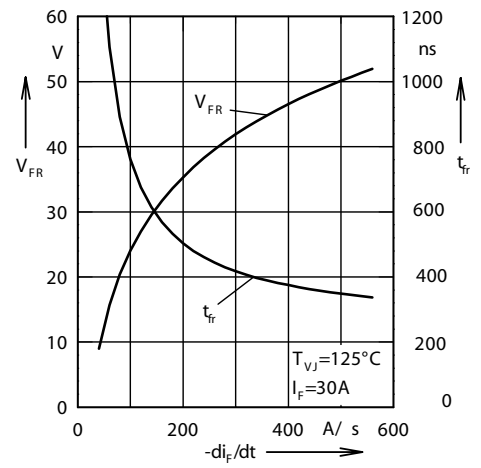


Fig. 6 Peak forward voltage versus di_F/dt .

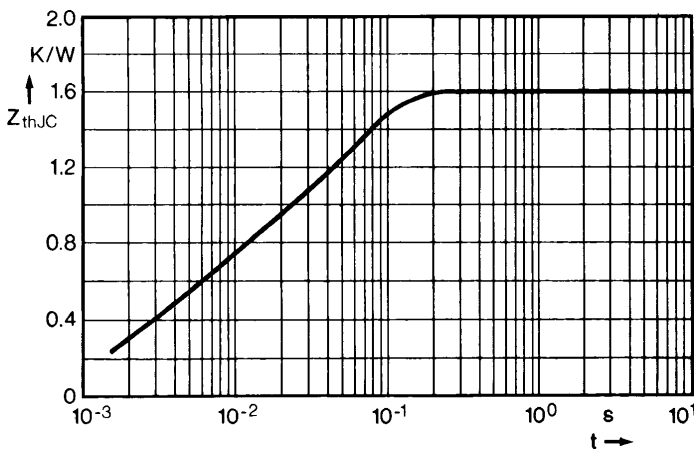


Fig. 7 Transient thermal impedance junction to case.